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InAs(P)/InP QDs as sources of single indistinguishable photons at 1.55 μm

D. A. Vajner¹, M. Wasiluk², P. Holewa^{2,3,4}, E. Zięba-Ostójk², M. von Helversen¹, A. Sakanas³, A. Huck⁵, K. Yvind^{3,4}, N. Gregersen³, A. Musiał², M. Syperek², E. Semenova^{3,4}, T. Heindel¹

1 – Institute of Solid State Physics, Technical University of Berlin, 10623 Berlin, Germany

2 – Department of Experimental Physics, Faculty of Fundamental Problems of Technology, Wrocław University of Science and Technology, Wyb. Wyspiańskiego 27, 50-370 Wrocław, Poland

3 – DTU Electro, Technical University of Denmark, 2800 Kongens Lyngby, Denmark

4 – NanoPhoton-Center for Nanophotonics, Technical University of Denmark, 2800 Kongens Lyngby, Denmark

5 – Center for Macroscopic Quantum States (bigQ), Department of Physics, Technical University of Denmark, 2800 Kgs. Lyngby, Denmark

maja.wasiluk@pwr.edu.pl

Epitaxial quantum dots (QDs) exhibit substantial promise as non-classical light sources in quantum technologies [1]. In particular, the generation of single, indistinguishable photons on demand is pivotal for advanced quantum cryptographic key exchange algorithms [2]. This study investigates the quantum optical characteristics of single photons emitted by InAs(P)/InP QDs heterogeneously integrated with silicon.

The investigated QDs, grown via metalorganic vapor-phase epitaxy in the Stranski-Krastanow mode, showcase the emission at $\sim 1.55 \mu\text{m}$ [3], indispensable for long-haul, low-loss optical transmission through standard silica fibers. The photon extraction efficiency is enhanced to $\sim 10\%$ by employing a metallic mirror beneath the QDs in combination with a top mesa structure [4]. Our study confirms the single-photon emission from the QDs through measurements of the second-order autocorrelation function, revealing $g^{(2)}(0) = 0.005(4)$ for biexciton under two-photon resonant excitation of the biexciton-exciton radiative cascade.

To investigate the degree of indistinguishability of emitted photons, we conducted also Hong-Ou-Mandel-type two-photon interference (TPI) experiment. The TPI visibility, quantifying the degree of indistinguishability of emitted photons, is crucial in examining the coherence of carriers within the QD [5]. Exciton-phonon interactions and carrier-carrier scattering significantly contribute to the degradation of coherence within the QDs. Using direct integration of the raw experimental data or fitting to a model, we evaluated the raw (i.e., ‘as measured’) and the post-selected TPI visibility up to 35% and 73%, respectively [6], which represents a state-of-the-art achievement for InAs/InP QDs emitting at $1.55 \mu\text{m}$. The significant progress in the generation of single indistinguishable photons in the telecom C-band offers crucial insights into their potential integration within quantum information technologies.

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